

Notice of References Cited	Application/Control No. 09/891,129	Applicant(s)/Patent Under Reexamination NISHIYAMA ET AL.	
	Examiner Anh D. Mai	Art Unit 2814	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-6291867	09-2001	Wallace et al.	257/410
	C	US-			
	D	US-			
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	F	US-			
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	A. Chatterjee et al., CMOS Metal Replacement Gate Transistors Using Tantalum Pentaoxide Gate Insulator. IEDM 1998, pp. 777-780.
	V	W. J. Qi et al., MOSCAP and MOSFET Characteristics Using ZrO ₂ Gate Dielectric Deposited Directly on Si. IEDM 1999, pp. 145-148.
	W	S. Inumiya et al., Conformable Formation of High Quality Ultra-Thin Amorphous Ta ₂ O ₅ Gate Dielectrics Utilizing Water Assisted Deposition (WAD) for Sub 50 nm Damascene Metal Gate MOSFETs. IEDM 2000, pp. 649-652.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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